

What is claimed is:

1. An apparatus, comprising:
a semiconductor substrate; and
first and second support structures formed on the substrate, the second support structure at least partially surrounding the first support structure on the substrate,
the first and second support structures each configured to support an electrical connector to be formed over the first and second support structures on the substrate.
2. The assembly of claim 1 wherein the first and second support structures each overlay electronic circuitry fabricated on a semiconductor die.
3. The assembly of claim 2 wherein the second support structure is electrically insulated from the first support structure, so as to reduce the capacitance generated between the second support structure and the electronic circuitry.
4. The assembly of claim 1 wherein the first support structure further comprises a substantially circular cross-section.
5. The assembly of claim 1 wherein the first support structure is made of aluminum.
6. The assembly of claim 1 wherein the second support structure further comprises a substantially annular cross-section located approximately concentric with the first support structure.
7. The assembly of claim 1 wherein the second support structure is made of aluminum.
8. The assembly of claim 1 wherein the semiconductor substrate has a geometric center, and wherein the first support structure further comprises a conductive element having at least a portion oriented toward said geometric center.

9. The assembly of claim 8 wherein the second support structure further comprises a substantially annular circumferential segment, the circumferential segment being located approximately concentric with the first support structure and electrically insulated from the conductive element.
10. An assembly for supporting an electrical connector with minimal parasitic capacitance, comprising:
- first and second pads formed on a semiconductor substrate, the first and second pads underlying a solder bump interconnect and overlaying electronic circuitry;
 - the second pad at least partially surrounding the first pad so as to support the solder bump interconnect; and
 - the second pad being electrically insulated from the first pad so as to reduce the capacitance generated between the second pad and the electronic circuitry.
11. The assembly of claim 10 wherein the first and second pads each overlay electronic circuitry fabricated on a semiconductor die.
12. The assembly of claim 10 wherein the first pad further comprises a substantially circular cross-section.
13. The assembly of claim 10 wherein the first pad is made of aluminum.
14. The assembly of claim 10 wherein the second pad further comprises a substantially annular cross-section located approximately concentric with the first pad.
15. The assembly of claim 10 wherein the second pad is made of aluminum.
16. The assembly of claim 10 wherein the semiconductor substrate has a geometric center, and wherein the first pad further comprises a conductive element having at least a portion oriented toward said geometric center.

17. The assembly of claim 16 wherein the second pad further comprises a substantially annular circumferential segment, the circumferential segment being located approximately concentric with the first pad and electrically insulated from the conductive element.

18. A method of supporting an electrical connector, comprising:

fabricating first and second pads on a semiconductor die, the first and second pads each overlaying electronic circuitry and each configured to support a solder bump interconnect; and

the second pad at least partially surrounding the first pad and electrically insulated from the first pad so as to reduce generation of capacitance between the second pad and the electronic circuitry.

19. The method of claim 18 further comprising overlaying the solder bump interconnect upon the first and second pads.

20. The method of claim 18 wherein the fabricating further comprises fabricating a first pad having a substantially circular cross-section.

21. The method of claim 18 wherein the fabricating further comprises fabricating an aluminum first pad.

22. The method of claim 18 wherein the forming further comprises forming a second pad located approximately concentric with the first pad, the second pad having a substantially annular cross-section.

23. The method of claim 18 wherein the fabricating further comprises fabricating an aluminum second pad.

24. The method of claim 18 wherein the fabricating further includes fabricating a first pad having a conductive element with at least a portion oriented toward the geometric center of the semiconductor die.

25. The method of claim 24 wherein the forming further includes forming a second pad having a substantially annular circumferential segment, the circumferential segment being located approximately concentric with the first pad and electrically insulated from the conductive element.